

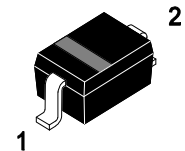
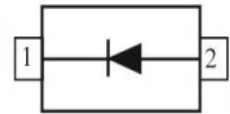


1N914W S High –Speed Switching Diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.

Marking: 5D



SOD323

2. MAXIMUM RATINGS(Ta = 25oC)

Parameter	Symbol	Limits	Unit
Reverse Voltage	VR	100	V
Forward Current	IF	200	mA
Peak Forward Surge Current	IFMS	500	mA

3. THERMAL CHARACTERISTICS

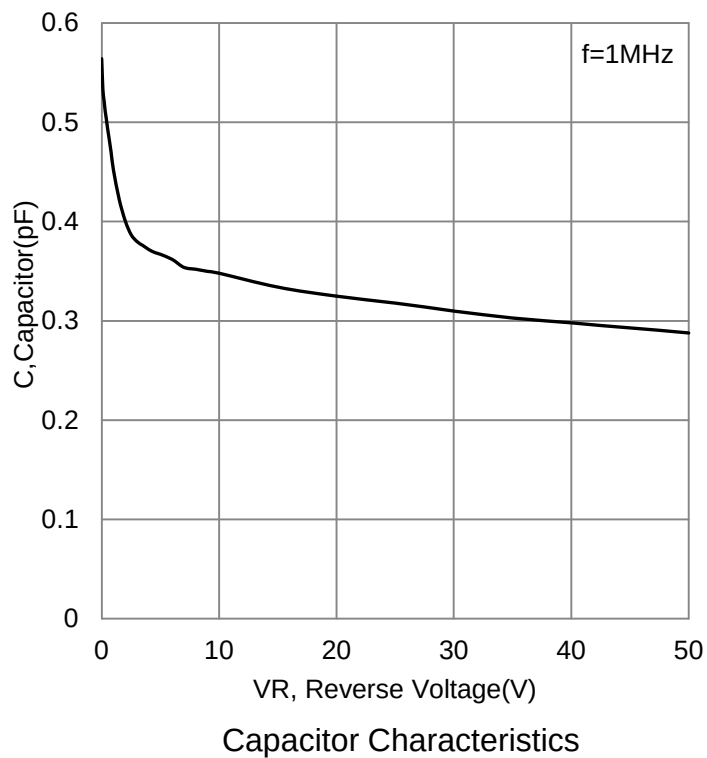
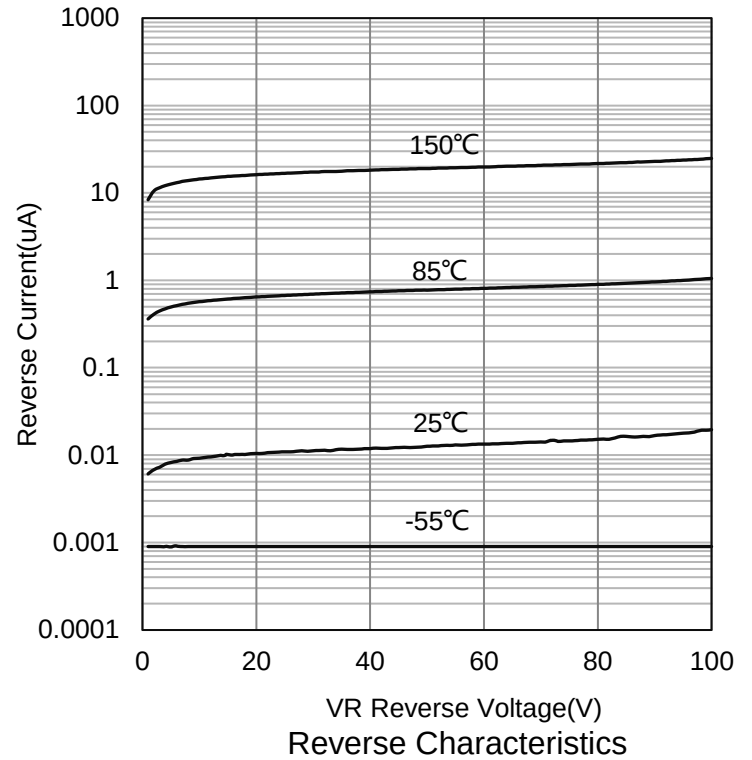
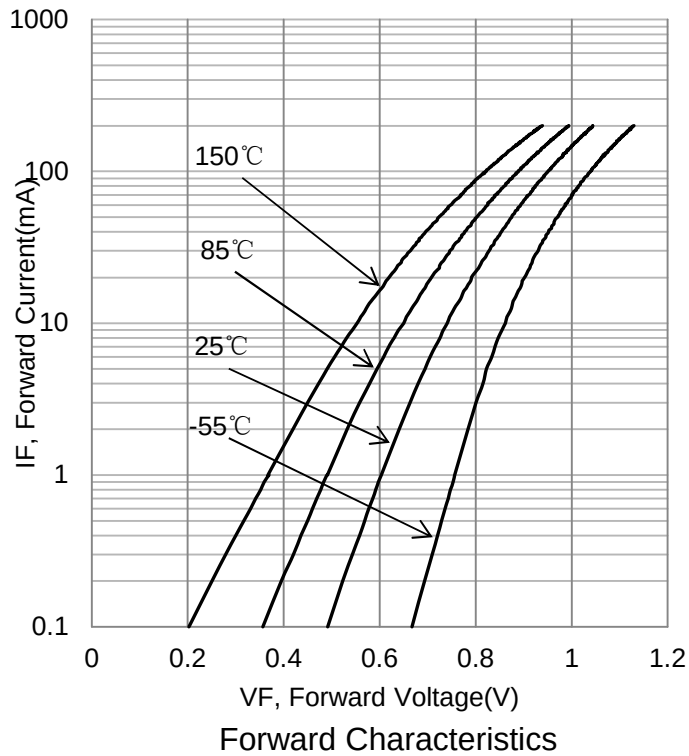
Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	200 1.57	mW mW/°C
Thermal Resistance, Junction-to-Ambient(Note 1)	RθJA	635	°C/W
Thermal Resistance, Junction-to-Case	RθJC	350	°C/W
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

4. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage (IR = 100μA)	VBR	100	-	-	V
Reverse Voltage Leakage Current (VR = 20V)	IR	-	-	25	nA
(VR = 75V)		-	-	5	μA
Diode Capacitance (VR = 0, f = 1.0 MHz)	CT	-	-	4	pF
Forward Voltage (IF = 10 mA)	VF	-	-	1	V
(IF = 50 mA)		-	-	1	
Reverse Recovery Time (IF = IR = 10 mA)	trr	-	-	4	ns
Non-Repetitive Peak Forward Current (square wave;Tj=25 °C prior to surge t=1 μs) (t=1ms) (t=1s)	IFSM	- -	- -	4 1	A



5. ELECTRICAL CHARACTERISTICS CURVES





PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

